

High Speed Infrared Emitting Diodes, 850 nm, Surface Emitter Technology

VSMY2850RGX01



VSMY2850GX01



21725-3

DESCRIPTION

VSMY2850X01 series are infrared, 850 nm emitting diodes based on GaAlAs surface emitter chip technology with extreme high radiant intensities, high optical power and high speed, molded in clear, untinted plastic packages (with lens) for surface mounting (SMD).

FEATURES

- Package type: surface mount
- Package form: GW, RGW
- Dimensions (L x W x H in mm): 2.3 x 2.3 x 2.8
- AEC-Q101 qualified
- Peak wavelength: $\lambda_p = 850$ nm
- High reliability
- High radiant power
- Very high radiant intensity
- Angle of half intensity: $\phi = \pm 10^\circ$
- Suitable for high pulse current operation
- Terminal configurations: gullwing or reserve gullwing
- Package matches with detector VEMD2500X01 series
- Floor life: 4 weeks, MSL 2a, acc. J-STD-020
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

AUTOMOTIVE
GRADERoHS
COMPLIANT
GREEN
[5-2008]**

APPLICATIONS

- IrDA compatible data transmission
- Miniature light barrier
- Photointerrupters
- Optical switch
- Emitter source for proximity sensors
- IR touch panels
- IR illumination

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	ϕ (deg)	λ_p (nm)	t_r (ns)
VSMY2850RGX01	100	± 10	850	10
VSMY2850GX01	100	± 10	850	10

Note

- Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
VSMY2850RGX01	Tape and reel	MOQ: 6000 pcs, 6000 pcs/reel	Reverse gullwing
VSMY2850GX01	Tape and reel	MOQ: 6000 pcs, 6000 pcs/reel	Gullwing

Note

- MOQ: minimum order quantity

** Please see document "Vishay Material Category Policy": www.vishay.com/doc?99902

VSMY2850RGX01, VSMY2850GX01



Vishay Semiconductor 威世半导体 High Speed Infrared Emitting Diodes,
850 nm, Surface Emitter Technology

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5$, $t_p = 100\ \mu\text{s}$	I_{FM}	200	mA
Surge forward current	$t_p = 100\ \mu\text{s}$	I_{FSM}	1	A
Power dissipation		P_V	190	mW
Junction temperature		T_j	100	$^{\circ}\text{C}$
Operating temperature range		T_{amb}	- 40 to + 85	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	- 40 to + 100	$^{\circ}\text{C}$
Soldering temperature	acc. figure 7, J-STD-020	T_{sd}	260	$^{\circ}\text{C}$
Thermal resistance junction/ambient	J-STD-051, soldered on PCB	R_{thJA}	250	K/W

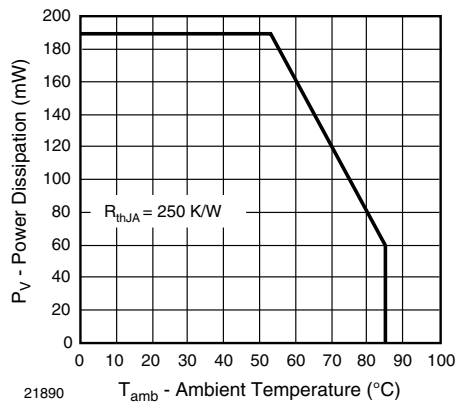


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

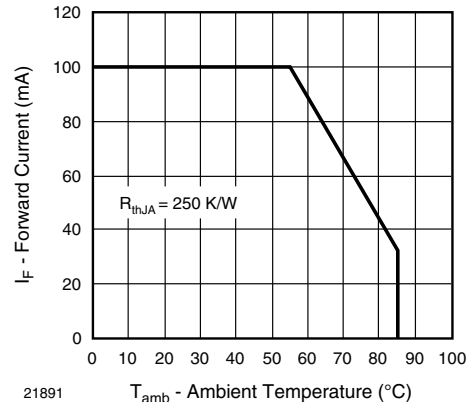


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100\ \text{mA}$, $t_p = 20\ \text{ms}$	V_F		1.65	1.9	V
	$I_F = 1\ \text{A}$, $t_p = 100\ \mu\text{s}$	V_F		2.9		V
Temperature coefficient of V_F	$I_F = 1\ \text{mA}$	TK_{VF}		- 1.45		mV/K
	$I_F = 10\ \text{mA}$	TK_{VF}		- 1.3		mV/K
Reverse current		I_R	not designed for reverse operation			μA
Junction capacitance	$V_R = 0\ \text{V}$, $f = 1\ \text{MHz}$, $E = 0\ \text{mW/cm}^2$	C_J		125		pF
Radiant intensity	$I_F = 100\ \text{mA}$, $t_p = 20\ \text{ms}$	I_e	50	100	150	mW/sr
	$I_F = 1\ \text{A}$, $t_p = 100\ \mu\text{s}$	I_e		850		mW/sr
Radiant power	$I_F = 100\ \text{mA}$, $t_p = 20\ \text{ms}$	ϕ_e		55		mW
Temperature coefficient of radiant power	$I_F = 100\ \text{mA}$	$TK\phi_e$		- 0.35		%/K
Angle of half intensity		ϕ		± 10		deg
Peak wavelength	$I_F = 100\ \text{mA}$	λ_p	840	850	870	nm
Spectral bandwidth	$I_F = 30\ \text{mA}$	$\Delta\lambda$		30		nm
Temperature coefficient of λ_p	$I_F = 30\ \text{mA}$	$TK\lambda_p$		0.25		nm/K
Rise time	$I_F = 100\ \text{mA}$, 20 % to 80 %	t_r		10		ns
Fall time	$I_F = 100\ \text{mA}$, 20 % to 80 %	t_f		10		ns
Virtual source diameter		d		1.5		mm

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

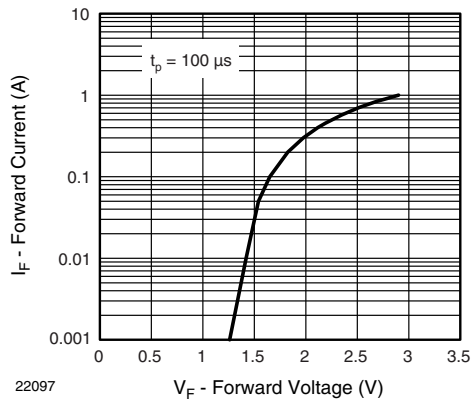


Fig. 3 - Forward Current vs. Forward Voltage

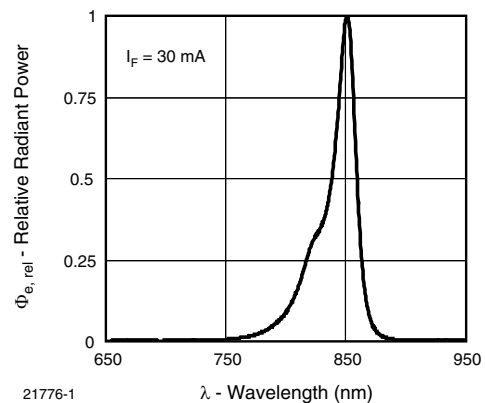


Fig. 5 - Relative Radiant Power vs. Wavelength

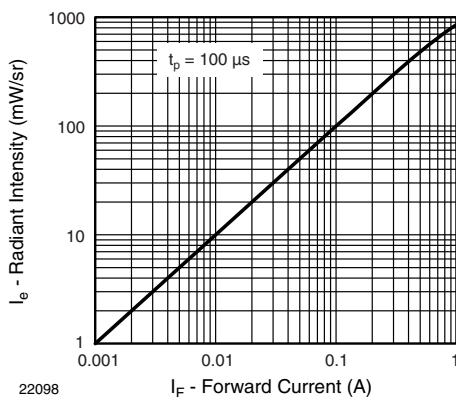


Fig. 4 - Radiant Intensity vs. Forward Current

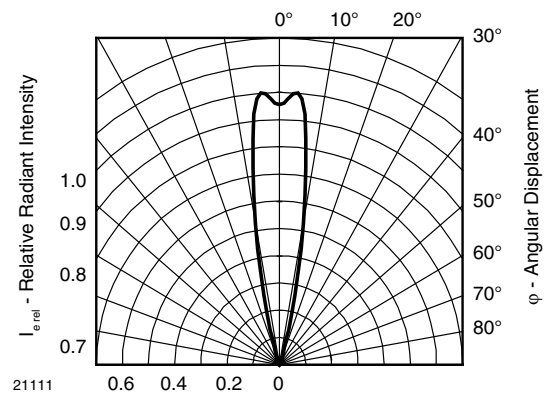


Fig. 6 - Relative Radiant Intensity vs. Angular Displacement

SOLDER PROFILE

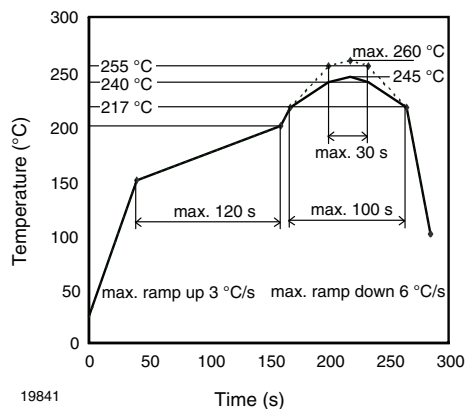


Fig. 7 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label:

Floor life: 4 weeks

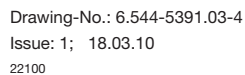
Conditions: $T_{amb} < 30\text{ }^{\circ}\text{C}$, RH < 60 %

Moisture sensitivity level 2a, acc. to J-STD-020.

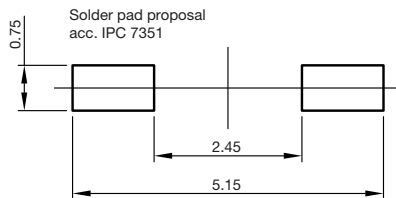
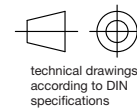
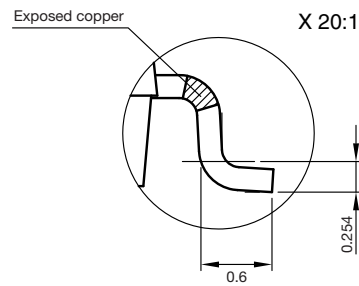
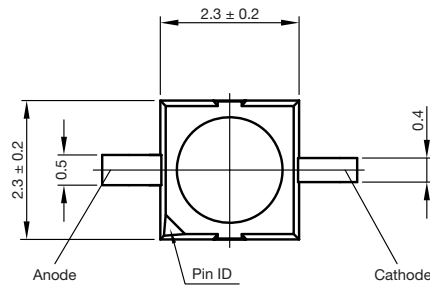
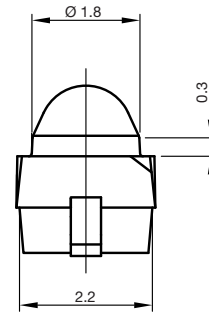
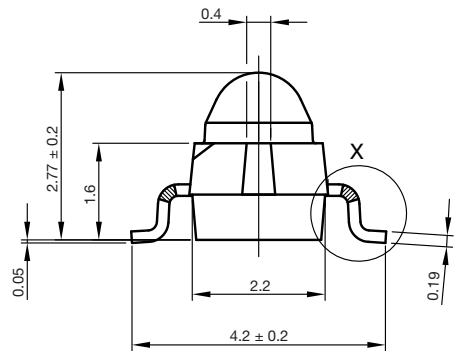
DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at $40\text{ }^{\circ}\text{C}$ (+ 5 $^{\circ}\text{C}$), RH < 5 %.

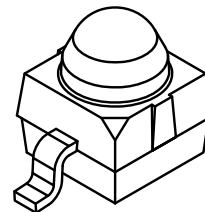
Viewing Semiconductor High Speed Infrared Emitting Diodes,
850 nm, Surface Emitter Technology



PACKAGE DIMENSIONS in millimeters: **VSMY2850GX01**

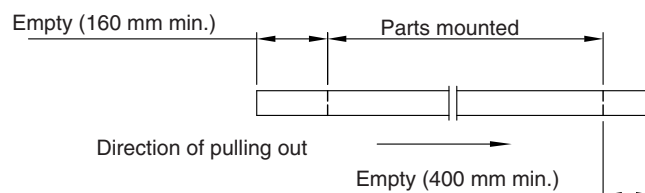


Not indicated tolerances ± 0.1



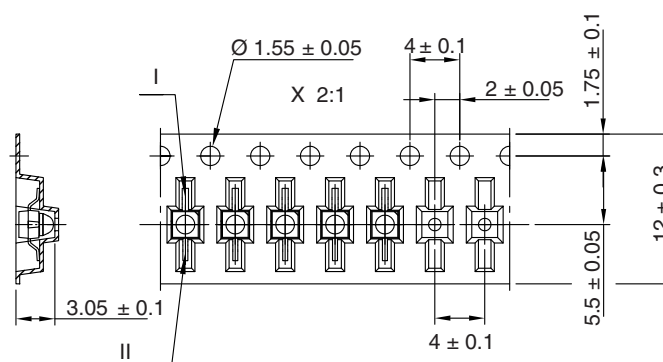
Drawing-No.: 6.544-5383.03-4
Issue: 1; 18.03.10
22099

Visay V Semiconductor Co., Ltd. High Speed Infrared Emitting Diodes,
850 nm, Surface Emitter Technology



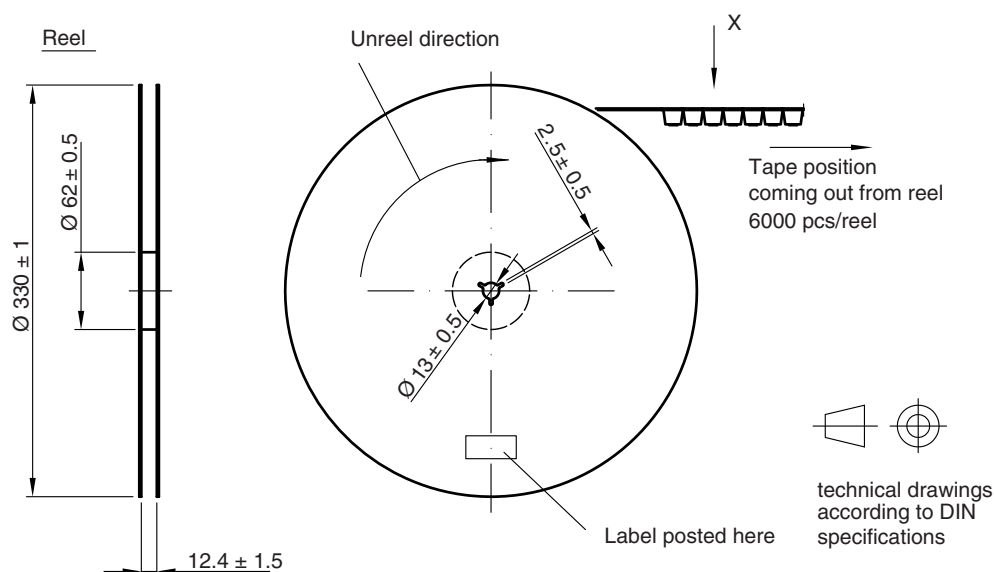
Terminal position in tape

Devicce	Lead I	Lead II
VENT2000	Collector	Emitter
VENT2500		
VEMD2000	Cathode	Anode
VEMD2500		
V SMB2000		
V SMG2000		
VSMY2850RG	Anode	Cathode

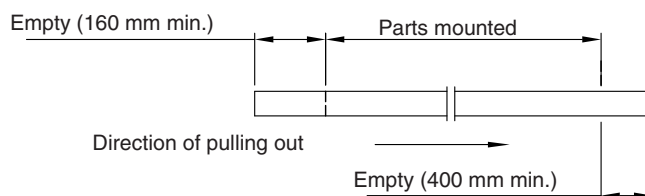


Drawing-No.: 9.800-5100.01-4
Issue: 2; 18.03.10
21572

TAPING AND REEL DIMENSIONS in millimeters: **VSMY2850GX01**

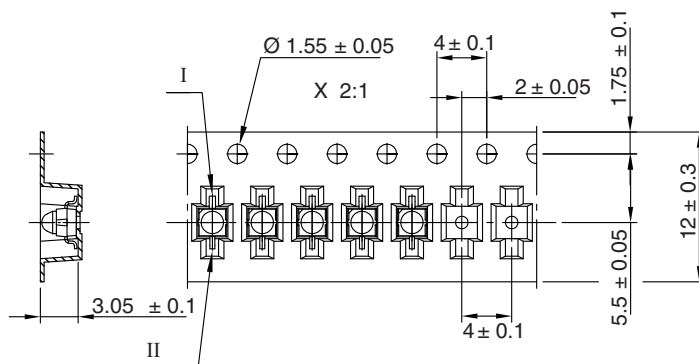


Leader and trailer tape:



Terminal position in tape

Device	Lead I	Lead II
VEMT2020	Collector	Emitter
VEMT2520		
VSMB2020	Cathode	Anode
VSMG2020		
VEMD2020		
VEMD2520		
VSMY2850G	Anode	Cathode



Drawing-No.: 9.800-5091.01-4

Issue: 3; 18.03.09

21571

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